

EXHIBIT H

JOHN P. TAYLOR
PATENT ATTORNEY
POST OFFICE BOX 1598
TEMECULA, CA 92593-1598
(909) 699-7551
(909) 699-7852 (Fax)

November 5, 1999

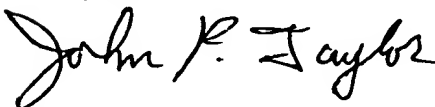
Dr. Sheldon Aronowitz, M.S. J-201
Dr. Valeriy Sukharev, M.S. J-201
Dr. John Haywood, M.S. J-202
Dr. James Kimball, M.S. J-202
Dr. Helmut Puchner, M.S. J-201
Dr. Ravindra Kapre, M.S. J-201
Dr. Nicholas Eib, M.S. J-202
LSI Logic Corporation
1551 McCarthy Blvd.
Milpitas, CA 95035

Re: First Draft of Patent Application
PROCESS FOR ETCHING A CONTROLLABLE
THICKNESS OF OXIDE ON AN INTEGRATED
CIRCUIT STRUCTURE ON A SEMICONDUCTOR
SUBSTRATE USING NITROGEN PLASMA AND
AN RF BIAS APPLIED TO THE SUBSTRATE
LSI Docket No. 99-039

Gentlemen:

Enclosed is a first draft of your above captioned patent application for your review. Please note that there are questions, comments and blanks to be filled in. Ralph Veseli of the LSI Logic Intellectual Property Department has requested that this application be filed before the end of the year. I will be out of the office from November 13-30, returning to the office on December 1. Therefore, if you can complete your review of the enclosed draft and send me your comments by that date, we should be able to finish up the case and have it filed in the USPTO before the holidays.

Regards,



John P. Taylor
Patent Attorney

Ralph R. Veseli, Patent Attorney LSI Logic Intellectual Property Department w/enclosure